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(Not for submission under 37 CFR 1.99)

Application Number	10595686
Filing Date	2006-12-27
First Named Inventor	CHOY et al.
Art Unit	2881
Examiner Name	
Attorney Docket Number	1751-0405

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10595686 - GAU: 4181

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/R.L./	5	Wen-Jun LI, et al., "Growth mechanism and growth habit of oxide crystals", Journal of Crystal Growth, 1999, pp. 186-196, Vol. 203, Elsevier Science B.V.	<input type="checkbox"/>
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/R.L./	7	J. F. MUTH, et al., "Excitonic structure and absorption coefficient measurements of ZnO single crystal epitaxial films deposited by pulsed laser deposition", Journal of Applied Physics, June 1, 1999, pp. 7884-7887, Vol. 85, No. 11, American Institute of Physics.	<input type="checkbox"/>
/R.L./	8	Ahmed NAHHAS, et al., "Epitaxial growth of ZnO films on Si substrates using an epitaxial GaN buffer", Applied Physics Letters, March 12, 2001, pp. 1511-1513, Vol. 78, No. 11, American Institute of Physics.	<input type="checkbox"/>

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/R.L./	9	W. I. PARK, et al., "Metal-organic vapor phase epitaxial growth of high-quality ZnO films on Al2O3(00-1)", Journal of Materials Research, May 2001, pp. 1358-1362, Vol. 16, No. 5, Materials Research Society. <input type="checkbox"/>
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/R.L./	12	Lionel VAYSSIERES, et al., "Purpose-Built Anisotropic Metal Oxide Material: 3D Highly Oriented Microrod Array of ZnO", Journal of Physical Chemistry, 2001, pp. 3350-3352, Vol. 105, American Chemical Society. <input type="checkbox"/>
/R.L./	13	B. WESSLER, et al., "Epitaxial growth of ZnO thin films on ScAlMgO4 (0001) by chemical solution deposition", Journal of Crystal Growth, 2002, pp. 283-292, Vol. 242, Elsevier Science B.V. <input type="checkbox"/>
/R.L./	14	Aishi YAMAMOTO, et al., "Biexciton luminescence in high-quality ZnO epitaxial thin films", Journal of Applied Physics, November 15, 2001, pp. 4973-4976, Vol. 90, No. 10, American Institute of Physics. <input type="checkbox"/>

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Signature	/gfr4/	Date (YYYY-MM-DD)	2007-07-24
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